AO3401

P-Channel Enhancement Mode MOSFET

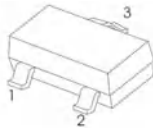
V_{DSS}	-30 V
I_D	-4.2A
$R_{DS(ON)}$	41 m Ω

FEATURES

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

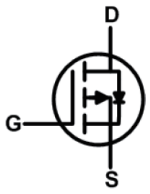
A19T

SOT-23



1. GATE
2. SOURCE
3. DRAIN

Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current-Continuous	-4.2	A
I_{DM}	Drain Current-Pulsed (Note 1)	-30	A
P_D	Maximum Power Dissipation	1.2	W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient (Note 2)	104	℃/W

Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-24V,V_{GS} = 0V			-1	μA
Gate-source leakage current	I_{GSS}	V_{GS} =±12V, V_{DS} = 0V			±100	nA
On characteristics						
Drain-source on-resistance (note 1)	$R_{DS(on)}$	V_{GS} =-10V, I_D =-4.2A		41	60	mΩ
		V_{GS} =-4.5V, I_D =-4A		47	70	mΩ
		V_{GS} =-2.5V,I_D=-1A		61	85	mΩ
Forward tranconductance (note 1)	g_{FS}	V_{DS} =-5V, I_D =-5A	7			S
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.7		-1.3	V
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	V_{DS} =-15V,V_{GS} =0V,f =1MHz		1050		pF
Output capacitance	C_{oss}			127		pF
Reverse transfer capacitance	C_{rss}			85		pF
Switching characteristics (note 2)						
Turn-on delay time	$t_{d(on)}$	V_{GS}=-10V,V_{DS}=-15V, R_L=3.6Ω,R_{GEN}=6Ω			6.5	ns
Turn-on rise time	t_r				3.5	ns
Turn-off delay time	$t_{d(off)}$				40	ns
Turn-off fall Time	t_f				13	ns
Drain-source diode characteristics and maximum ratings						
Diode forward voltage (note 1)	V_{SD}	I_S=-1A,V_{GS}=0V			-1	V

Note :

1. Pulse Test : Pulse width≤300μs, duty cycle≤2%.
2. These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES

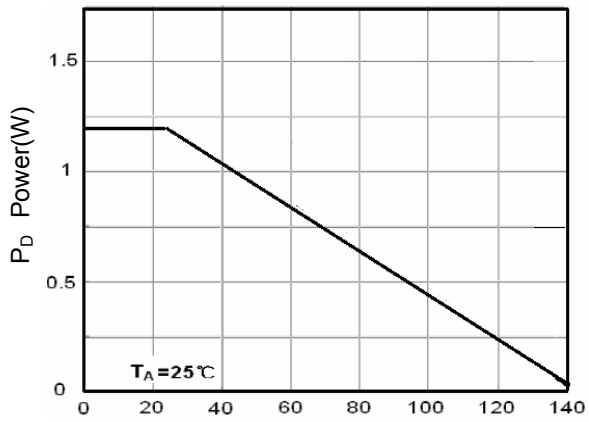


Figure 1 Power Dissipation

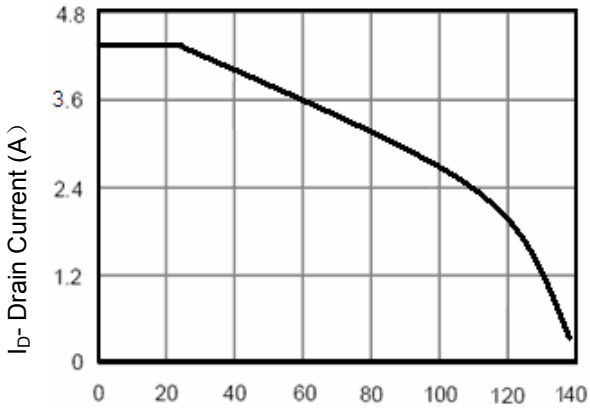


Figure 2 Drain Current

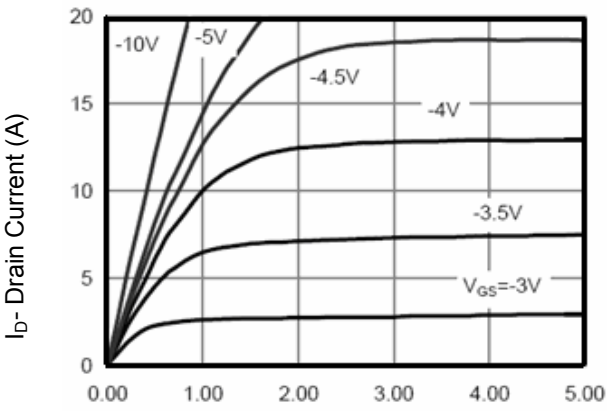


Figure 3 Output Characteristics

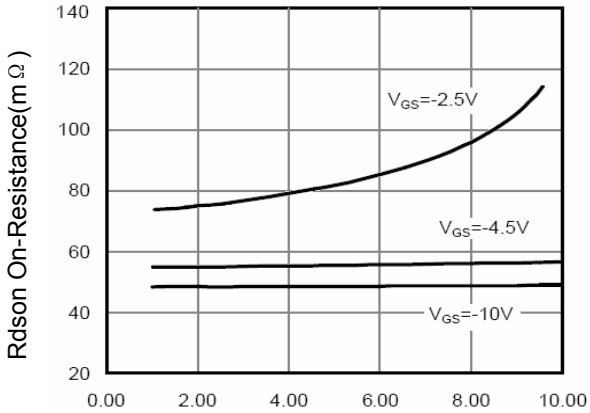


Figure 4 Drain-Source On-Resistance

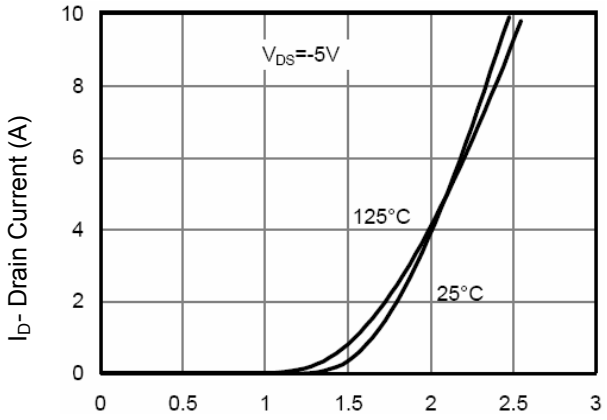


Figure 5 Transfer Characteristics

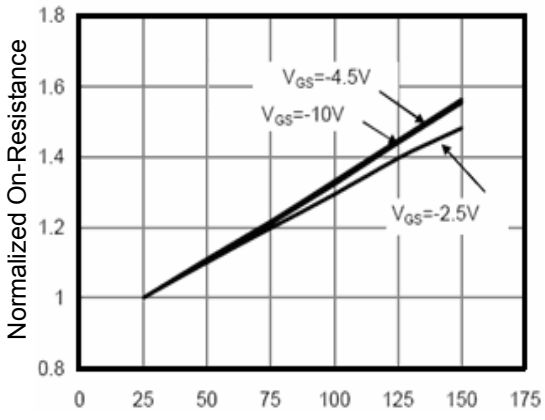


Figure 6 Drain-Source On-Resistance

RATING AND CHARACTERISTIC CURVES

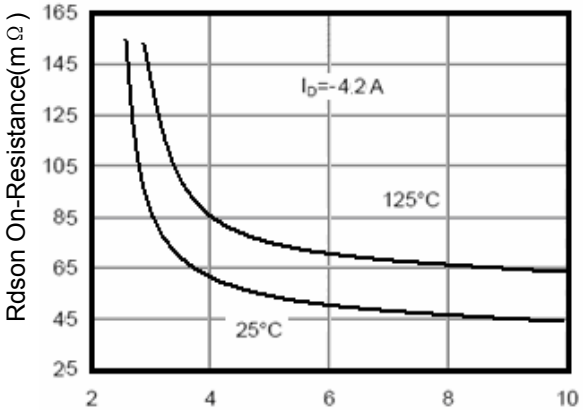


Figure 7 Rdson vs Vgs

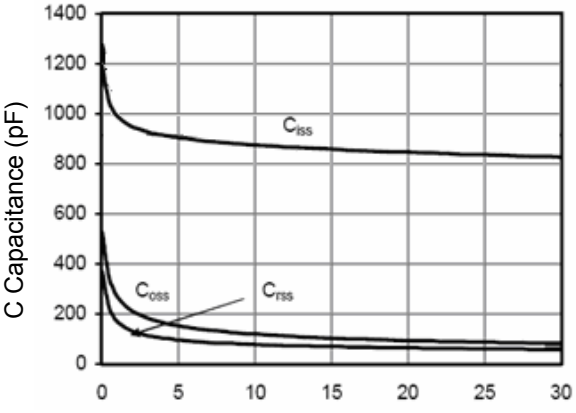


Figure 8 Capacitance vs Vds

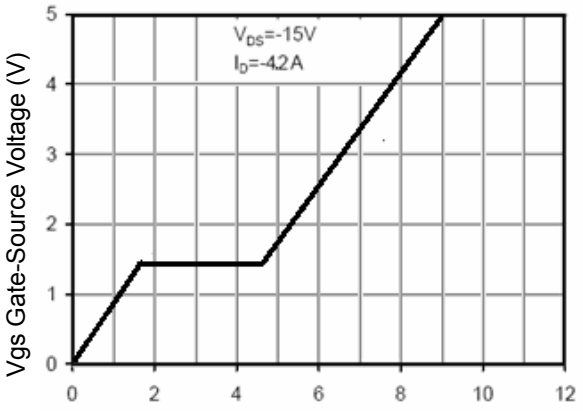


Figure 9 Gate Charge

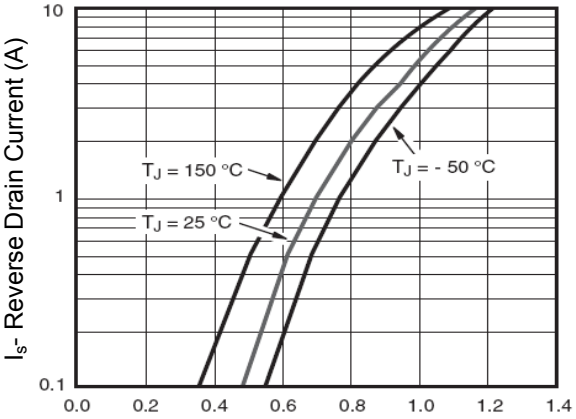


Figure 10 Source- Drain Diode Forward

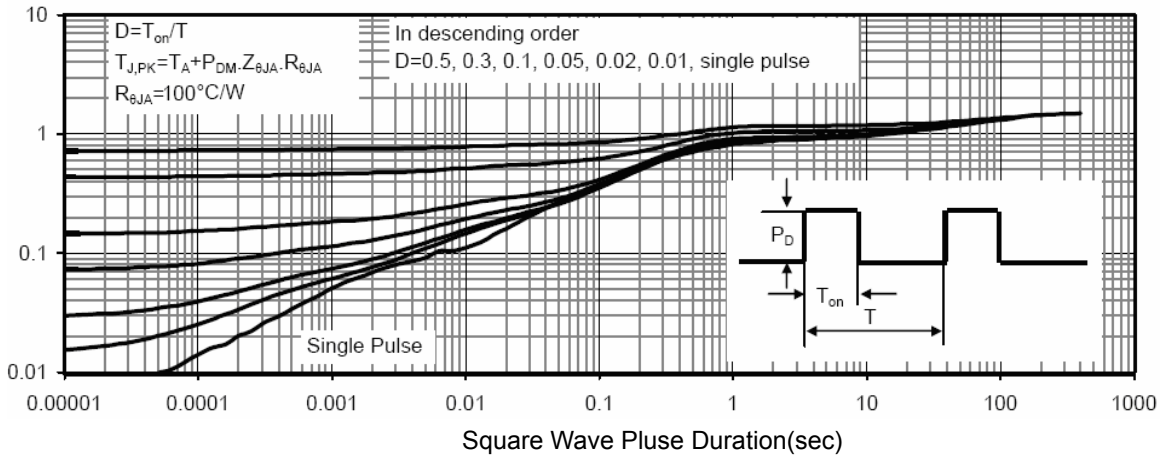
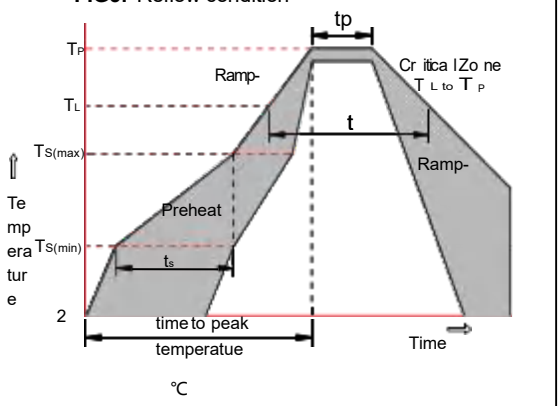


Figure 14 Normalized Maximum Transient Thermal Impedance

Soldering parameters

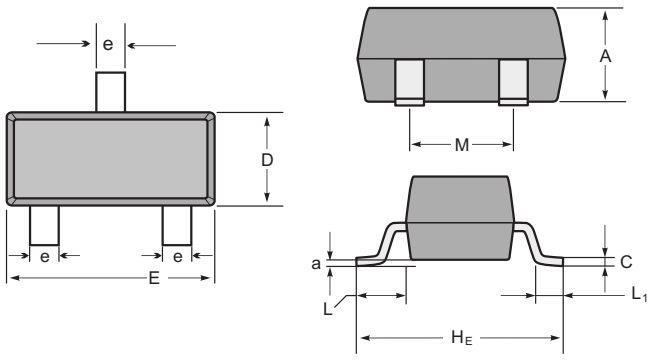
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

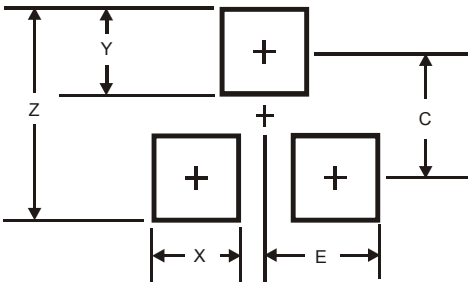
FIG5: Reflow condition



Package Dimensions & Suggested Pad Layout

SOT23





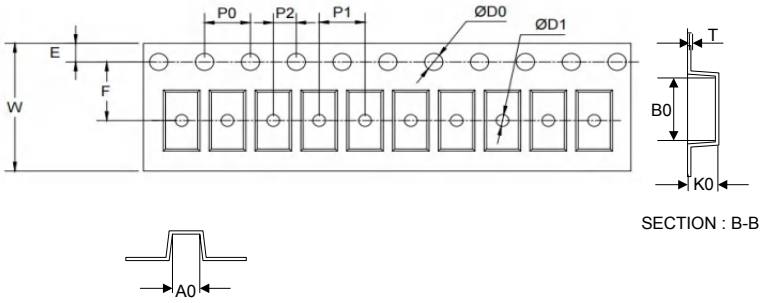
SOT-23 mechanical data

UNIT		A	C	D	E	H_E	e	M	L	L_1	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Tape & rell specification

Tape

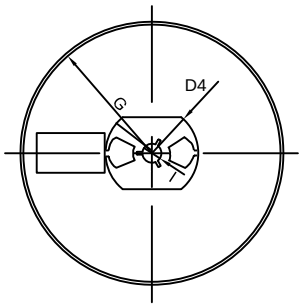


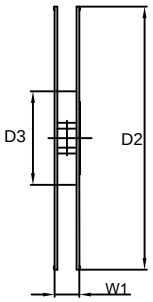
SECTION : B-B

SECTION : A-A

Symbol	Dimension (mm)
P0	4.00±0.10
P1	4.00±0.10
P2	2.00±0.10
D0	1.55±0.10
D1	1.05±0.10
E	1.55±0.10
F	3.60±0.10
W	8.00±0.10
A0	3.80±0.20
B0	3.25±0.20
K0	1.45±0.10
T	0.25±0.05

7” Reel





D2	178.0±3.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0
Quantity: 3000PCS	